

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







J110

JFET - General Purpose

N-Channel - Depletion

N-Channel Junction Field Effect Transistors, depletion mode (Type A) designed for general purpose audio amplifiers, analog switches and choppers.

Features

- N-Channel for Higher Gain
- Drain and Source Interchangeable
- High AC Input Impedance
- High DC Input Resistance
- Low $R_{DS(on)} \le 18 \Omega$
- Fast Switching $t_{d(on)} + t_r = 8.0 \text{ ns (Typ)}$
- Low Noise $\overline{en} = 6.0 \text{ nV}/\sqrt{\text{Hz}}$ @ 10 Hz (Typ)
- Pb-Free Packages are Available*

MAXIMUM RATINGS

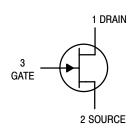
Rating	Symbol	Value	Unit
Gate-Source Voltage	VG _S	-25	Vdc
Drain-Gate Voltage	V_{DG}	-25	Vdc
Gate Current	I _G	10	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	310 2.82	mW mW/°C
Operating Junction Temp Range	TJ	135	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



ON Semiconductor®

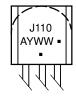
http://onsemi.com



MARKING DIAGRAM



CASE 29 TO-92 (TO-226) STYLE 5



J110 = Device Code

= Assembly Location

= Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
J110	TO-92	1000 Units / Box
J110G	TO-92 (Pb-Free)	1000 Units / Box
J110RLRA	TO-92	2000 / Tape & Reel
J110RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

				T	
Characteristic		Symbol	Min	Max	Unit
STATIC CHARACTERISTICS					
Gate-Source Breakdown Voltage	$(I_G = -1.0 \mu Adc)$	V _{(BR)GSS}	-25	-	Vdc
Gate Reverse Current (V _G	$(V_{GS} = -15 \text{ Vdc}, V_{DS} = 0)$ $V_{SS} = -15 \text{ Vdc}, V_{DS} = 0, T_{A} = 100^{\circ}\text{C}$	I _{GSS}	- -	-3.0 -200	nAdc
Gate-Source Cutoff Voltage	$(V_{DS} = 5.0 \text{ Vdc}, I_D = 1.0 \mu\text{Adc})$	$V_{GS(off)}$	-0.5	-4.0	Vdc
Drain Source On-Resistance	$(V_{DS} \le 0.1 \text{ V}, V_{GS} = 0 \text{ V})$	R _{DS(on)}	-	18	Ω
Zero-Gate-Voltage Drain Current (Note 1)	(V _{DS} = 15 Vdc)	I _{DSS}	10	_	mAdc
DYNAMIC CHARACTERISTICS					
Drain-Gate and Source-Gate On-Capacitance ($V_{DS} = V_{GS} = 0$, f = 1.0 MHz)	e _	$\begin{matrix} C_{dg(on)} \\ + \\ C_{sg(on)} \end{matrix}$	-	85	pF
Drain-Gate Off-Capacitance	$(V_{GS} = -10 \text{ Vdc}, f = 1.0 \text{ MHz})$	C _{dg(off)}	-	15	pF
Source-Gate Off-Capacitance	(V _{GS} = -10 Vdc, f = 1.0 MHz)	C _{sg(off)}	-	15	pF

^{1.} Pulse Width = 300 μ s, Duty Cycle = 3.0%.

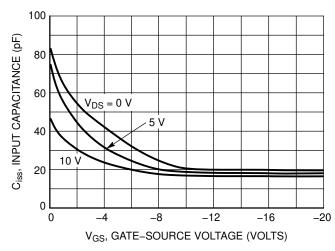


Figure 1. Common Source Input Capacitance versus Gate-Source Voltage

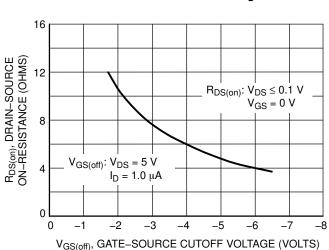


Figure 3. On-Resistance versus Gate-Source Cutoff Voltage

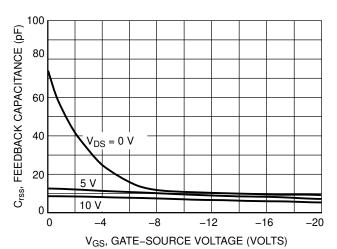


Figure 2. Common Source Reverse Feedback Capacitance versus Gate-Source Voltage

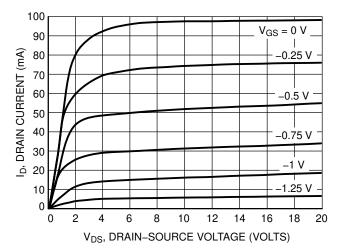
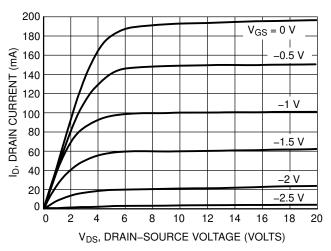
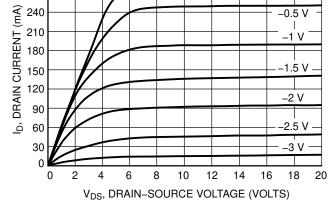


Figure 4. Output Characteristic $V_{GS(off)} = -2.0 \text{ V}$

300

270





 $V_{GS} = 0 V$

Figure 5. Output Characteristic $V_{GS(off)} = -3.0 \text{ V}$

Figure 6. Output Characteristic $V_{GS(off)} = -4.0 \text{ V}$

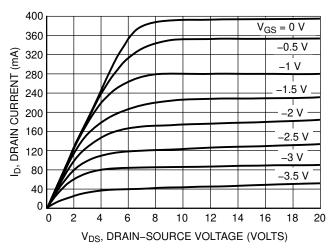
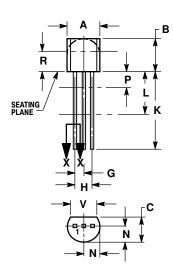
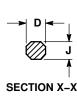


Figure 7. Output Characteristic $V_{GS(off)} = -5.0 \text{ V}$

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 5:

PIN 1 DRAIN

- SOURCE 2.
- GATE

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA **Phone**: 480–829–7710 or 800–344–3860 Toll Free USA/Canada **Fax**: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.